



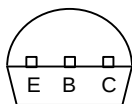
Micro Commercial Components
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2SC2216

Features

- Capable of 300mWatts of Power Dissipation.
- Collector-current 50mA
- Collector-base Voltage 50V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration
Bottom View



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

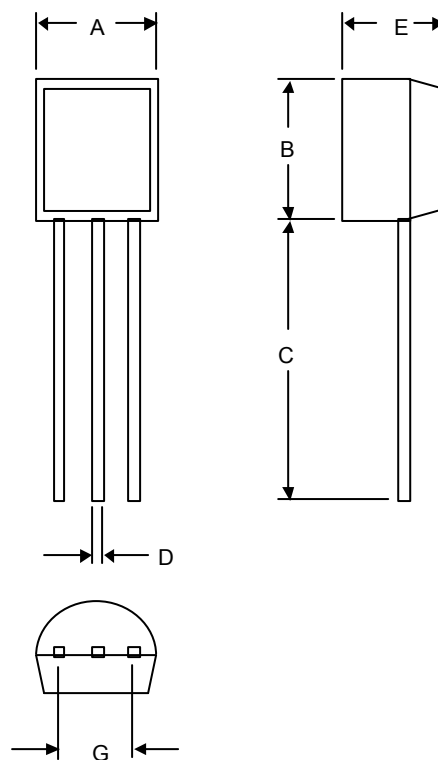
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=10\text{mA}$, $I_B=0$)	45	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu\text{A}$, $I_E=0$)	50	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu\text{A}$, $I_C=0$)	4.0	---	Adc
I_{CBO}	Collector Cutoff Current ($V_{CB}=50\text{Vdc}$, $I_E=0$)	---	0.1	μA
I_{EBO}	Emitter Cutoff Current ($V_{EB}=4.0\text{Vdc}$, $I_C=0$)	---	0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=12.5\text{mA}$, $V_{CE}=12.5\text{Vdc}$)	40	140	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=15\text{mA}$, $I_B=1.5\text{mA}$)	---	0.2	Vdc
$V_{(BE)sat}$	Base-Emitter Saturation Voltage ($I_C=15\text{mA}$, $I_B=1.5\text{mA}$)	---	1.5	Vdc
fT	Transition Frequency ($V_{CE}=12.5\text{Vdc}$, $I_C=12.5\text{mA}$, f=100MHz)	300	---	MHz

NPN Silicon Plastic-Encapsulate Transistor

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	